TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type ( $L^2$ - $\pi$ -MOSV)

## **2SJ377**

# Relay Drive, DC/DC Converter and Motor Drive Applications

4 V gate drive

• Low drain–source ON-resistance :  $R_{DS\ (ON)}$  = 0.16  $\Omega$  (typ.)

High forward transfer admittance : |Y<sub>fS</sub>| = 4.0 S (typ.)
 Low leakage current : I<sub>DSS</sub> = -100 μA (max) (V<sub>DS</sub> = -60 V)

• Enhancement mode :  $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA})$ 

#### Maximum Ratings (Ta = 25°C)

Characteri	stic	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-60	V
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	-60	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	DC (Note 1)	$I_{D}$	-5	Α
	Pulse (Note 1)	I <sub>DP</sub>	-20	Α
Drain power dissipation	n (Tc = 25°C)	$P_{D}$	20	W
Single-pulse avalanche	e energy (Note 2)	E <sub>AS</sub>	273	mJ
Avalanche current		I <sub>AR</sub>	-5	Α
Repetitive avalanche e	nergy (Note 3)	E <sub>AR</sub>	2	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature ra	ange	T <sub>stg</sub>	-55~150	°C

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	6.25	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	125	°C/W

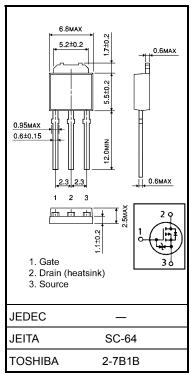
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = -25 V,  $T_{ch}$  = 25°C (initial), L = 14.84 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = -5 A

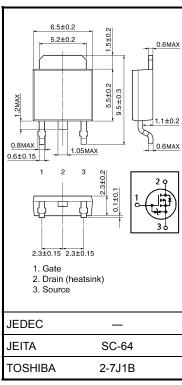
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.36 g (typ.)



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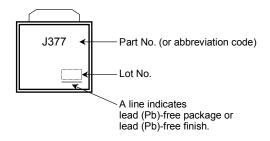
## **Electrical Characteristics (Ta = 25°C)**

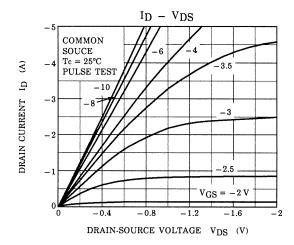
Charac	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Drain cutoff curr	ent	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V	_	_	-100	μΑ
Drain-source br	eakdown voltage	V <sub>(BR) DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	_	_	V
Gate threshold v	oltage/	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	_	-2.0	V
Drain-source ON-resistance		R <sub>DS (ON)</sub>	$V_{GS} = -4 \text{ V}, I_D = -2.5 \text{ A}$	_	0.24	0.28	Ω
			$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	_	0.16	0.19	
Forward transfer	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.5 A	2.0	4.0	_	S
Input capacitano	e	C <sub>iss</sub>			630	_	
Reverse transfe	r capacitance	C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		95	_	pF
Output capacitance		C <sub>oss</sub>		_	290	_	
Switching time	Rise time	t <sub>r</sub>	$V_{GS} \stackrel{OV}{\longrightarrow} I_{D} = -2.5A \\ V_{OUT} \stackrel{V}{\longrightarrow} R_{L} = 12\Omega \\ V_{DD} = -30V$	_	25	_	
	Turn-on time	t <sub>on</sub>		_	45	_	ns
	Fall time	t <sub>f</sub>		l	55		
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , $t_{\mathbf{W}} = 10 \mu \text{s}$	1	200	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	22	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx -48 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$		16		nC
Gate-drain ("Miller") charge		$Q_{gd}$			6		

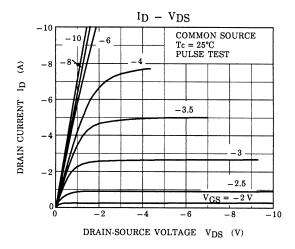
### Source-Drain Ratings and Characteristics (Ta = 25°C)

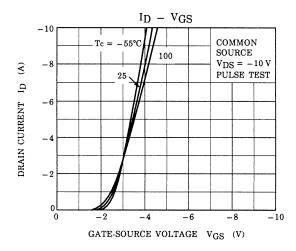
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	-5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	-20	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = -5 A, V <sub>GS</sub> = 0 V	_	_	1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = -5 A, V <sub>GS</sub> = 0 V	_	80	_	ns
Reverse recovery charge	Qrr	dl <sub>DR</sub> / dt = 50 A / μS	_	0.1	_	μC

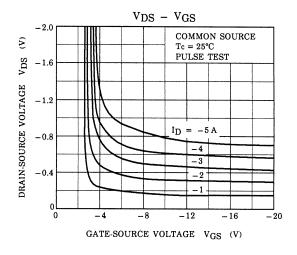
## Marking

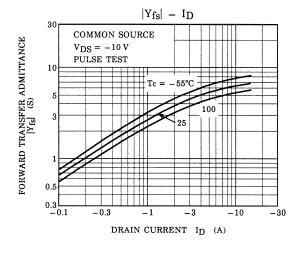


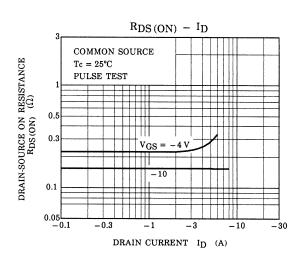




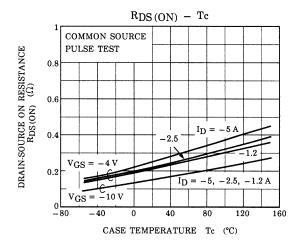


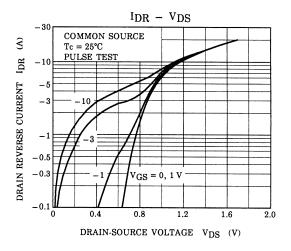


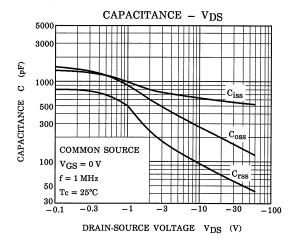


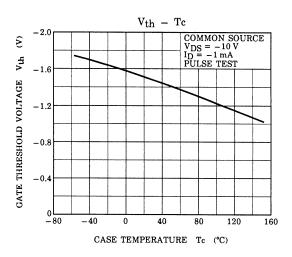


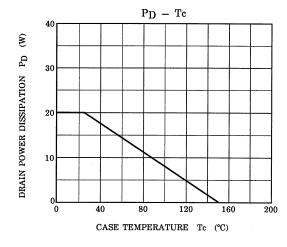
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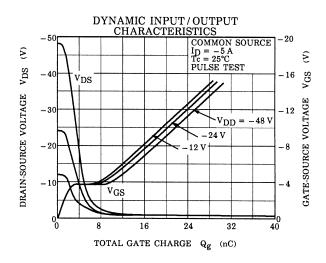


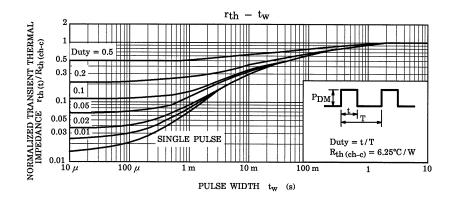


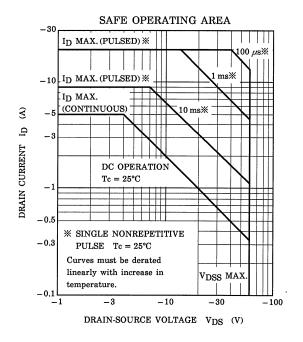


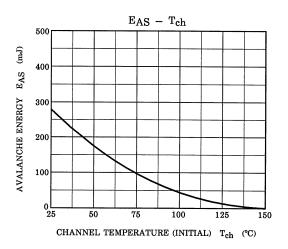


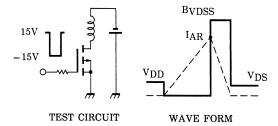












$$\begin{array}{ll} R_G \!=\! 25\Omega \\ V_{DD} \!=\! -25V, \; L \!=\! 14.84 mH \end{array} \quad E_{AS} \!=\! \frac{1}{2} \cdot L \cdot I^2 \cdot (\frac{B_{VDSS}}{B_{VDSS} \!-\! V_{DD}} \end{array}$$

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